

**KM68512B Family****Advance  
CMOS SRAM****Document Title****64Kx8 bit Low Power CMOS Static RAM****Revision History**

<b><u>Revision No.</u></b>	<b><u>History</u></b>	<b><u>Draft Data</u></b>	<b><u>Remark</u></b>
0.0	Initial draft	January 10th 1998	Advance

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## KM68512B Family

### 64Kx8 bit Low Power CMOS Static RAM

#### FEATURES

- Process Technology : 0.4  $\mu$ m CMOS
- Organization : 64Kx8
- Power Supply Voltage : Single 5V  $\pm$ 10%
- Low Data Retention Voltage : 2V(Min)
- Three state output and TTL Compatible
- Package Type : 32-TSOP I -0820F

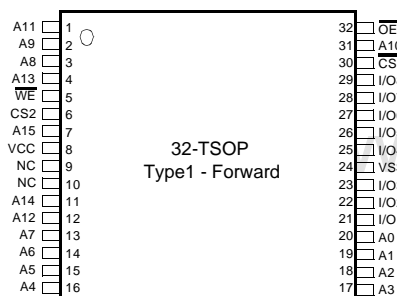
#### GENERAL DESCRIPTION

The KM68512B family is fabricated by SAMSUNG 's advanced CMOS process technology. The family support various operating temperature ranges and small package type for user flexibility of system design. The family also support low data retention voltage for battery back-up operation with low data retention current.

#### PRODUCT FAMILY

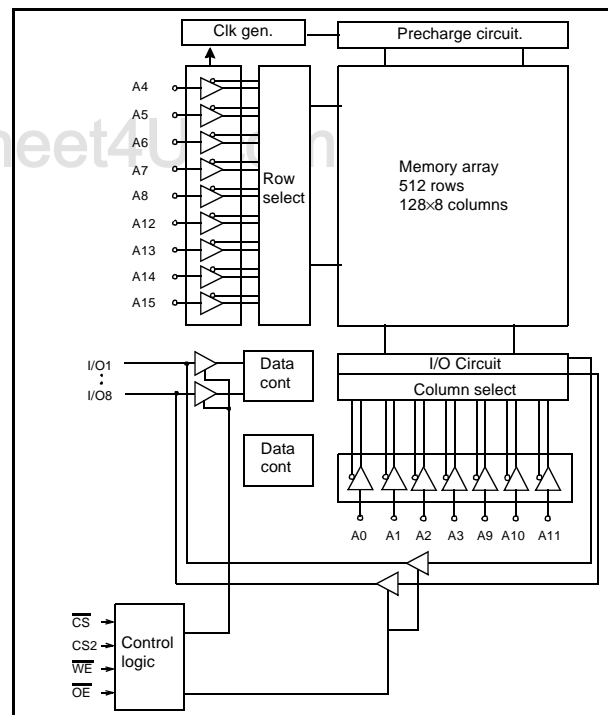
Product Family	Operating Temperature	Vcc Range	Speed(ns)	Power Dissipation		PKG Type
				Standby (Isb1, Max)	Operating (Icc2, Max)	
KM68512BL-L	Commercial(0~70°C)	5V $\pm$ 0.5V	55/70	10 $\mu$ A	60mA	32-TSOP1-F
KM68512BLI-L	Industrial(-40~85°C)		70	15 $\mu$ A		

#### PIN DESCRIPTION



Name	Function
A0~A15	Address Inputs
$\overline{WE}$	Write Enable Input
$\overline{CS1}$ , CS2	Chip Select Inputs
$\overline{OE}$	Output Enable Input
I/O1~I/O8	Data Inputs/Outputs
Vcc	Power
Vss	Ground
N.C	No Connection

#### FUNCTIONAL BLOCK DIAGRAM



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**KM68512B Family**
**PRODUCT LIST**

Commercial Temperature Product (0~70°C)		Industrial Temperature Products (-40~85°C)	
Part Name	Function	Part Name	Function
KM68512BLT-5L	32-TSOP1-F, 55ns, LL-pwr	KM68512BLTI-7L	32-TSOP1-F, 70ns, LL-pwr
KM68512BLT-7L	32-TSOP1-F, 70ns, LL-pwr		

**FUNCTIONAL DESCRIPTION**

$\overline{CS}_1$	$CS_2$	$\overline{OE}$	$\overline{WE}$	I/O Pin	Mode	Power
H	X <sup>1)</sup>	X <sup>1)</sup>	X <sup>1)</sup>	High-Z	Deselected	Standby
X <sup>1)</sup>	L	X <sup>1)</sup>	X <sup>1)</sup>	High-Z	Deselected	Standby
L	H	H	H	High-Z	Output Disabled	Active
L	H	L	H	Dout	Read	Active
L	H	X	L	Din	Write	Active

1. X means don't care. (Must be low or high state)

**ABSOLUTE MAXIMUM RATINGS <sup>1)</sup>**

Item	Symbol	Ratings	Unit	Remark
Voltage on any pin relative to Vss	V <sub>IN</sub> , V <sub>OUT</sub>	-0.5 to 7.0	V	-
Voltage on Vcc supply relative to Vss	V <sub>CC</sub>	-0.5 to 7.0	V	-
Power Dissipation	P <sub>D</sub>	1.0	W	-
Storage temperature	T <sub>STG</sub>	-65 to 150	°C	-
Operating Temperature	T <sub>A</sub>	0 to 70	°C	KM68512BL
		-40 to 85	°C	KM68512BLI
Soldering temperature and time	T <sub>SOLDER</sub>	260°C, 10sec(Lead Only)	-	-

1. Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation should be restricted to recommended operating condition. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

**KM68512B Family**
**RECOMMENDED DC OPERATING CONDITIONS** <sup>1)</sup>

Item	Symbol	Min	Typ	Max	Unit
Supply voltage	V <sub>CC</sub>	4.5	5.0	5.5	V
Ground	V <sub>SS</sub>	0	0	0	V
Input high voltage	V <sub>IH</sub>	2.2	-	V <sub>CC</sub> +0.5V <sup>2)</sup>	V
Input low voltage	V <sub>IL</sub>	-0.5 <sup>3)</sup>	-	0.8	V

**Note**

- Commercial Product : T<sub>A</sub>=0 to 70°C, unless otherwise specified  
Industrial Product : T<sub>A</sub>=-40 to 85°C, unless otherwise specified
- Overshoot : V<sub>CC</sub>+3.0V in case of pulse width≤30ns
- Undershoot : -3.0V in case of pulse width≤30ns
- Overshoot and undershoot is sampled, not 100% tested

**CAPACITANCE** <sup>1)</sup> (f=1MHz, T<sub>A</sub>=25°C)

Item	Symbol	Test Condition	Min	Max	Unit
Input capacitance	C <sub>IN</sub>	V <sub>IN</sub> =0V	-	6	pF
Input/Output capacitance	C <sub>IO</sub>	V <sub>IO</sub> =0V	-	8	pF

- Capacitance is sampled, not 100% tested

**DC AND OPERATING CHARACTERISTICS**

Item	Symbol	Test Conditions	Min	Typ	Max	Unit
Input leakage current	I <sub>LI</sub>	V <sub>IN</sub> =V <sub>SS</sub> to V <sub>CC</sub>	-1	-	1	μA
Output leakage current	I <sub>LO</sub>	$\overline{CS}_1=V_{IH}$ or $CS_2=V_{IL}$ or $\overline{OE}=V_{IH}$ or $\overline{WE}=V_{IL}$ , V <sub>IO</sub> =V <sub>SS</sub> to V <sub>CC</sub>	-1	-	1	μA
Operating power supply	I <sub>CC</sub>	I <sub>IO</sub> =0mA, $\overline{CS}_1=V_{IL}$ , CS <sub>2</sub> =V <sub>IH</sub> , V <sub>IN</sub> =V <sub>IL</sub> or V <sub>IH</sub> , Read	-	7	10	mA
Average operating current	I <sub>CC1</sub>	Cycle time=1μs, 100% duty, I <sub>IO</sub> =0mA	Read	-	5	mA
		$\overline{CS}_1 \leq 0.2V$ , CS <sub>2</sub> ≥V <sub>CC</sub> -0.2V, V <sub>IN</sub> ≤0.2V or V <sub>IN</sub> ≥V <sub>CC</sub> -0.2V	Write	-	30	mA
			I <sub>CC2</sub>	Cycle time=Min, 100% duty, I <sub>IO</sub> =0mA, $\overline{CS}_1=V_{IL}$ , CS <sub>2</sub> =V <sub>IH</sub> , V <sub>IN</sub> =V <sub>IL</sub> or V <sub>IH</sub>	-	-
Output low voltage	V <sub>OL</sub>	I <sub>OL</sub> =2.1mA	-	-	0.4	V
Output high voltage	V <sub>OH</sub>	I <sub>OH</sub> =-1.0mA	2.4	-	-	V
Standby Current (TTL)	I <sub>SB</sub>	$\overline{CS}_1=V_{IH}$ , CS <sub>2</sub> =V <sub>IL</sub> , Other inputs =V <sub>IL</sub> or V <sub>IH</sub>	-	-	3	mA
Standby Current (CMOS)	I <sub>SB1</sub>	$\overline{CS}_1 \geq V_{CC}-0.2V$ , CS <sub>2</sub> ≥V <sub>CC</sub> -0.2V or CS <sub>2</sub> ≤0.2V	-	1	10 <sup>1)</sup>	μA

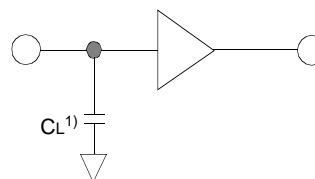
- Industrial product = 15μA

## KM68512B Family

### AC OPERATING CONDITIONS

#### TEST CONDITIONS ( Test Load and Input/Output Reference)

Input pulse level : 0.8 to 2.4V  
 Input rising and falling time : 5ns  
 Input and output reference voltage :1.5V  
 Output load(see right) :  $C_L=100\text{pF}+1\text{TTL}$



1. Including scope and jig capacitance

### AC CHARACTERISTICS ( $V_{CC}=4.5\sim 5.5\text{V}$ , KM68512B Family : $T_A=0$ to $70^\circ\text{C}$ , KM68512BI Family : $T_A=-40$ to $85^\circ\text{C}$ )

Parameter List		Symbol	Speed Bins				Units
			55ns		70ns		
			Min	Max	Min	Max	
Read	Read cycle time	t <sub>RC</sub>	55	-	70	-	ns
	Address access time	t <sub>AA</sub>	-	55	-	70	ns
	Chip select to output	t <sub>CO</sub>	-	55	-	70	ns
	Output enable to valid output	t <sub>OE</sub>	-	25	-	35	ns
	Chip select to low-Z output	t <sub>LZ</sub>	10	-	10	-	ns
	Output enable to low-Z output	t <sub>OLZ</sub>	5	-	5	-	ns
	Chip disable to high-Z output	t <sub>HZ</sub>	0	20	0	25	ns
	Output disable to high-Z output	t <sub>OHZ</sub>	0	20	0	25	ns
	Output hold from address change	t <sub>OH</sub>	10	-	10	-	ns
Write	Write cycle time	t <sub>WC</sub>	55	-	70	-	ns
	Chip select to end of write	t <sub>CW</sub>	45	-	60	-	ns
	Address set-up time	t <sub>AS</sub>	0	-	0	-	ns
	Address valid to end of write	t <sub>AW</sub>	45	-	60	-	ns
	Write pulse width	t <sub>WP</sub>	40	-	55	-	ns
	Write recovery time	t <sub>WR</sub>	0	-	0	-	ns
	Write to output high-Z	t <sub>WHZ</sub>	0	20	0	25	ns
	Data to write time overlap	t <sub>DW</sub>	20	-	30	-	ns
	Data hold from write time	t <sub>DH</sub>	0	-	0	-	ns
		End write to output low-Z	t <sub>OW</sub>	5	-	5	-

### DATA RETENTION CHARACTERISTICS

Item	Symbol	Test Condition	Min	Typ	Max	Unit	
V <sub>CC</sub> for data retention	V <sub>DR</sub>	$\overline{CS}_1 \geq V_{CC}-0.2\text{V}$	2.0	-	5.5	V	
Data retention current	I <sub>DR</sub>	$V_{CC}=3.0\text{V}$ , $\overline{CS}_1 \geq V_{CC}-0.2\text{V}$	KM68512BL-L	-	0.5	10	$\mu\text{A}$
			KM68512BLI-L	-	-	15	
Data retention set-up time	t <sub>SDR</sub>	See data retention waveform	0	-	-	ms	
Recovery time	t <sub>RDR</sub>		5	-	-		

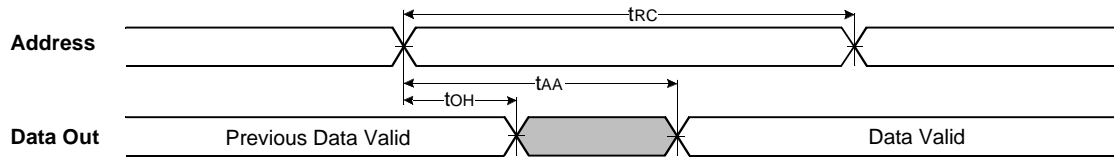
1.  $\overline{CS}_1 \geq V_{CC}-0.2\text{V}$ ,  $CS_2 \geq V_{CC}-0.2\text{V}$  ( $\overline{CS}_1$  controlled) or  $CS_2 \leq 0.2\text{V}$  ( $CS_2$  controlled).

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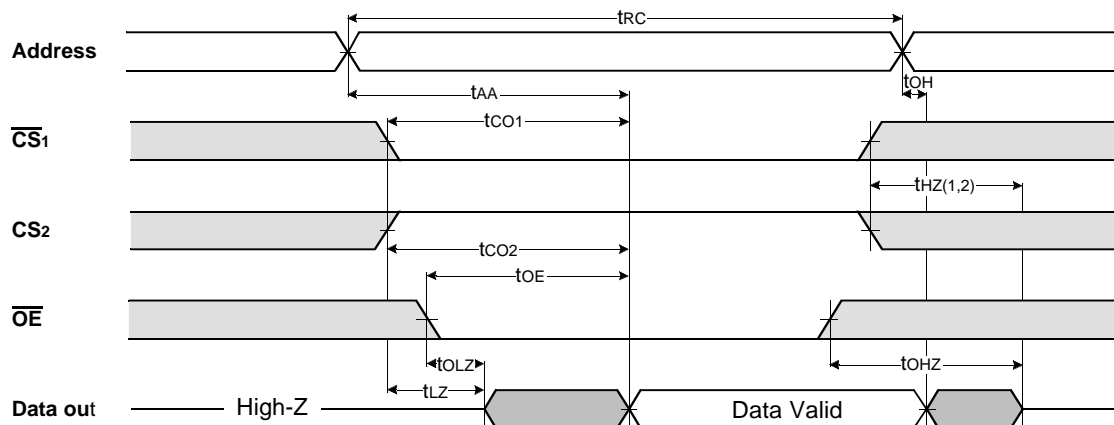
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**CMOS SRAM**

## TIMMING DIAGRAMS

**TIMING WAVEFORM OF READ CYCLE(1)** (Address Controlled,  $\overline{CS}=\overline{OE}=V_{IL}$ ,  $\overline{WE}=V_{IH}$ )



**TIMING WAVEFORM OF READ CYCLE(2)** ( $\overline{WE}=V_{IH}$ )



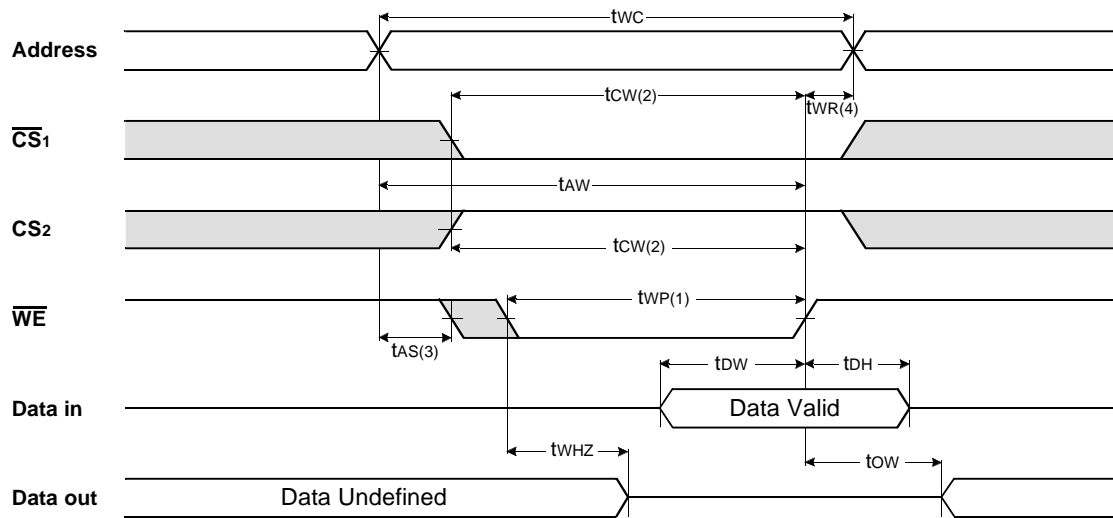
### NOTES (READ CYCLE)

1.  $t_{HZ}$  and  $t_{OHZ}$  are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels.
2. At any given temperature and voltage condition,  $t_{HZ}(\text{Max.})$  is less than  $t_{LZ}(\text{Min.})$  both for a given device and from device to device interconnection.

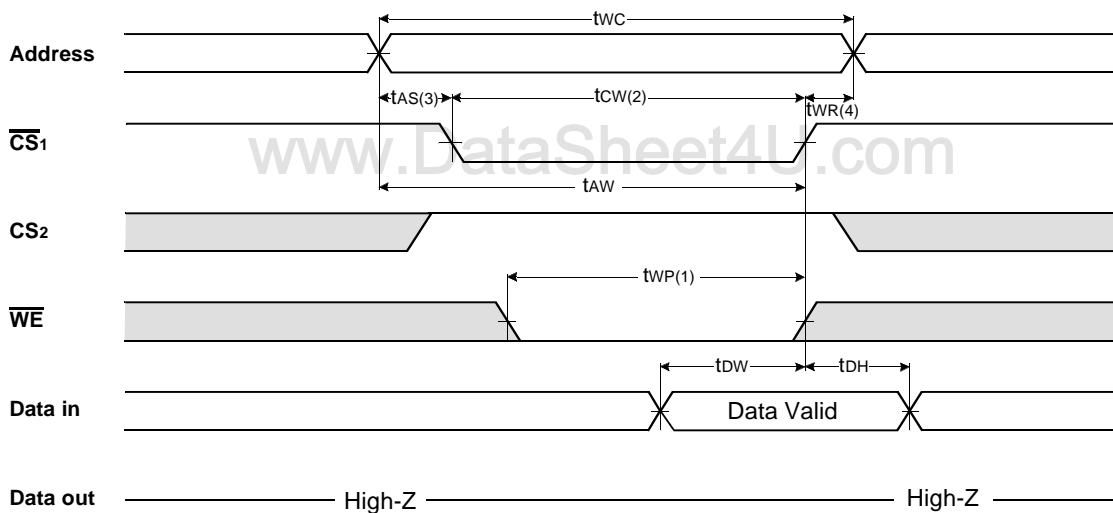
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## TIMING WAVEFORM OF WRITE CYCLE(1) ( $\overline{WE}$ Controlled)



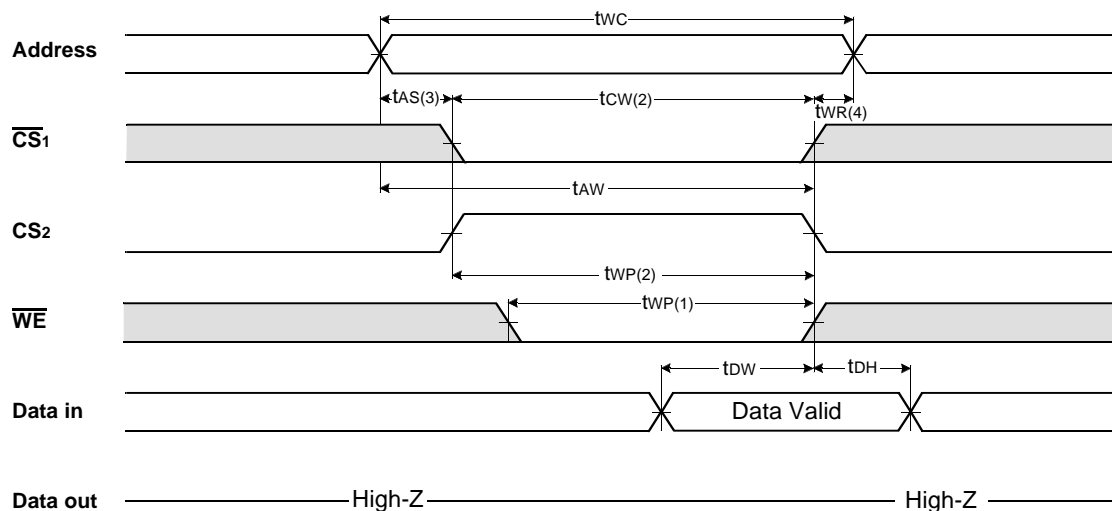
## TIMING WAVEFORM OF WRITE CYCLE(2) ( $\overline{CS_1}$ Controlled)



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## TIMING WAVEFORM OF WRITE CYCLE(3) ( $\overline{CS}_1$ Controlled)

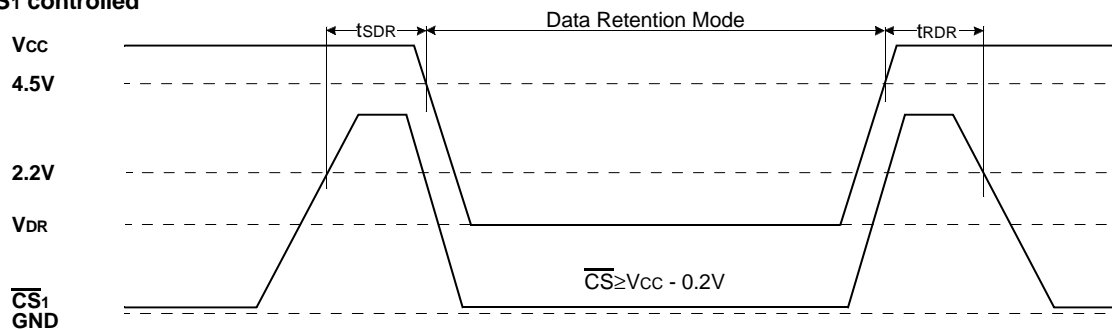


### NOTES (WRITE CYCLE)

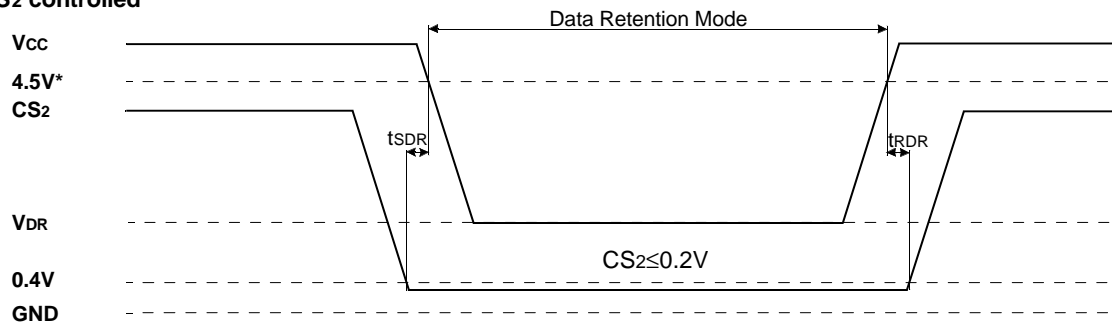
1. A write occurs during the overlap of a low  $\overline{CS}_1$ , a high  $CS_2$  and a low  $\overline{WE}$ . A write begins at the latest transition among  $\overline{CS}_1$  going low,  $CS_2$  going high and  $\overline{WE}$  going low. A write ends at the earliest transition among  $\overline{CS}_1$  going high,  $CS_2$  going low and  $\overline{WE}$  going high.  $t_{WP}$  is measured from the beginning of write to the end of write.
2.  $t_{CW}$  is measured from the  $\overline{CS}_1$  going low or  $CS_2$  going high to the end of write.
3.  $t_{AS}$  is measured from the address valid to the beginning of write.
4.  $t_{WR}$  is measured from the end of write to the address change.  $t_{WR(1)}$  applied in case a write ends as  $\overline{CS}_1$  or  $\overline{WE}$  going high.  $t_{WR(2)}$  applied in case a write ends as  $CS_2$  going to low.

## DATA RETENTION WAVE FORM

### $\overline{CS}_1$ controlled



### $CS_2$ controlled



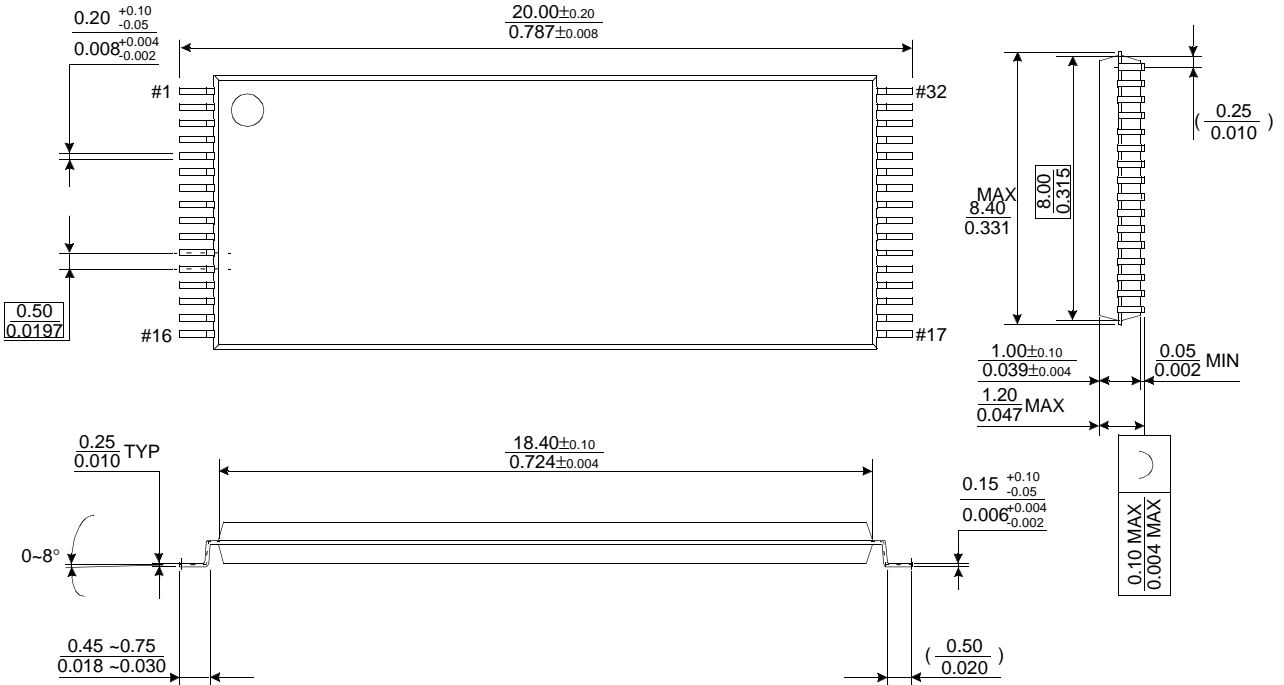


**KM68512B Family**

**PACKAGE DIMENSIONS**

Units : Millimeters(Inches)

**32-THIN SMALL OUTLINE PACKAGE TYPE I (0820F)**



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